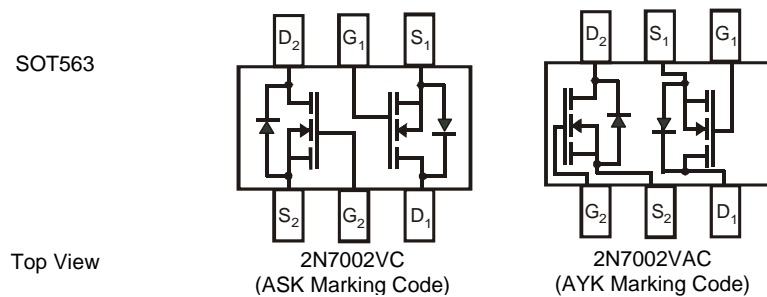


**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**
**Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

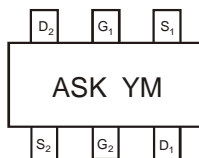
**Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram (Note 3)
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)

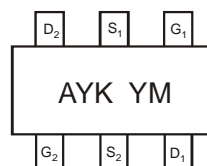

**Ordering Information (Note 4)**

Part Number	Case	Packaging
2N7002VC-7	SOT563	3000/Tape & Reel
2N7002VAC-7	SOT563	3000/Tape & Reel

- Notes:
1. No purposefully added Lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
  4. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**


ASK = 2N7002VC Product Type Marking Code (See Note 1)  
 YM = Date Code Marking  
 Y = Year ex: R = 2004  
 M = Month ex: 9 = September



AYK = 2N7002VAC Product Type Marking Code (See Note 1)  
 YM = Date Code Marking  
 Y = Year ex: R = 2004  
 M = Month ex: 9 = September

**Date Code Key**

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	R	S	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ	V <sub>DGR</sub>	60	V
Gate-Source Voltage (Note 5)	V <sub>GSS</sub>	Continuous	±20
		Pulsed	±40
Drain Current (Note 5)	I <sub>D</sub>	280	mA
Drain Current (Note 5)	I <sub>DM</sub>	1.5	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
				500		
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTIC (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	7.5	Ω	V <sub>GS</sub> = 5V, I <sub>D</sub> = 0.05A, V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A, T <sub>J</sub> = 125°C
				13.5		
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.0	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	5.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	—	20	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150Ω,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	—	20	ns	V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω

- Notes:
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com>.
  - Short duration pulse test used to minimize self-heating effect.

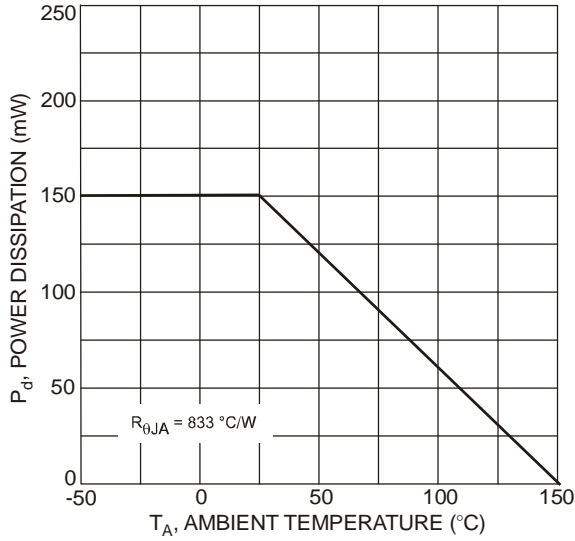
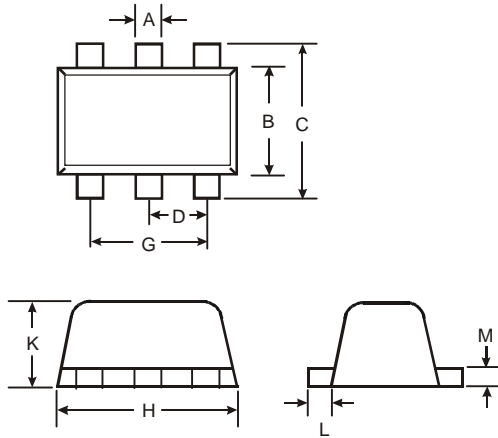


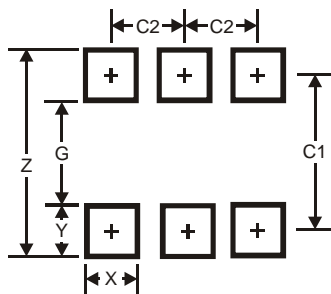
Fig. 1, Derating Curve - Total

**Package Outline Dimensions**



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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